

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
-30V	19m Ω @ $V_{GS} = -10\text{V}$	-8.7A
	45m Ω @ $V_{GS} = -4.5\text{V}$	-5.5A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

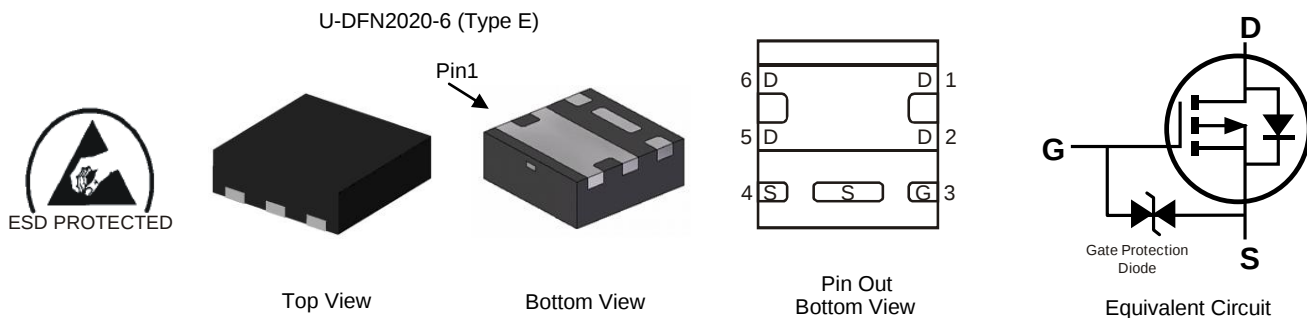
- Battery Management Application
- Power Management Functions
- DC-DC Converters

Features and Benefits

- 0.6mm profile – ideal for low profile applications
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: U-DFN2020-6 (Type E)
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe.
Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.007 grams (Approximate)

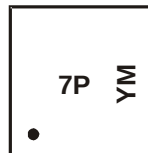


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3026SFDE-7	U-DFN2020-6 (Type E)	3,000/Tape & Reel
DMP3026SFDE-13	U-DFN2020-6 (Type E)	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



7P = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: D = 2016)
 M = Month (ex: 9 = September)

Date Code Key

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023
Code	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-8.7 -6.9	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	-10.4 -8.4	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	-50	A
Continuous Source-Drain Diode Current (Note 6)		T _A = +25°C	I _S	-2.0	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-23	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	27	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.72	W
	T _A = +70°C		0.46	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	175	°C/W
	t < 10s		121	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.0	W
	T _A = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	61	°C/W
	t < 10s		42	
Thermal Resistance, Junction to Case (Note 6)	Steady state	R _{θJC}	9.3	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	μA	V _{DS} = -24V, V _{GS} = 0V
Zero Gate Voltage Drain Current T _J = +150°C (Note 9)		—	—	-100		
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-1	—	-3	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	15	19	mΩ	V _{GS} = -10V, I _D = -4.5A
			28	45		V _{GS} = -4.5V, I _D = -3.5A
			34	54		V _{GS} = -4.0V, I _D = -3.0A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1,204	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	154	—		
Reverse Transfer Capacitance	C _{rss}	—	112	—		
Gate Resistance	R _g	—	16	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -10V)	Q _g	—	19.6	—	nC	V _{DS} = -15V, I _D = -9.5A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	9.2	—		
Gate-Source Charge	Q _{gs}	—	4.3	—		
Gate-Drain Charge	Q _{gd}	—	3.9	—		
Turn-On Delay Time	t _{D(on)}	—	5.3	—	ns	V _{DS} = -15V, V _{GS} = -10V, R _G = 6Ω, I _D = -9.5A
Turn-On Rise Time	t _r	—	23	—		
Turn-Off Delay Time	t _{D(off)}	—	34	—		
Turn-Off Fall Time	t _f	—	26	—		
Reverse Recovery Time	t _{rr}	—	10	—	ns	I _F = -9.5A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{rr}	—	3.3	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = 25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

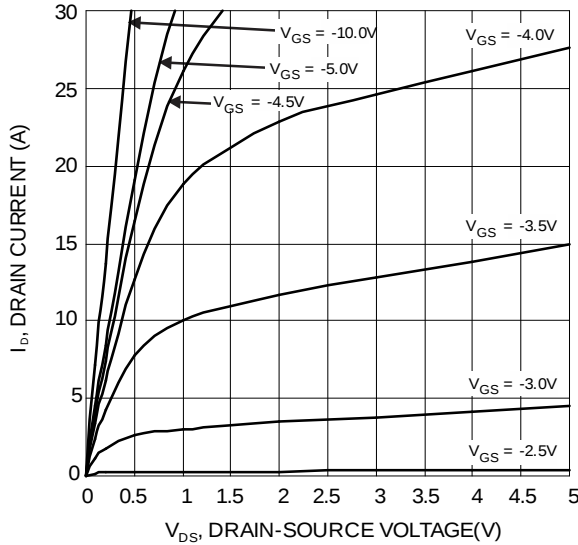


Figure 1 Typical Output Characteristic

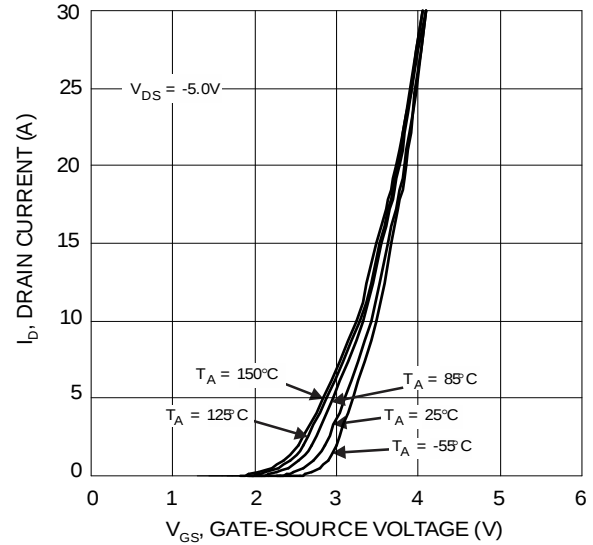


Figure 2 Typical Transfer Characteristic

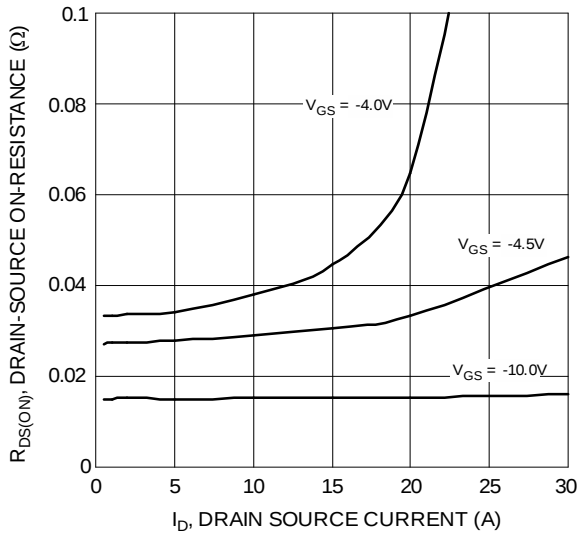


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

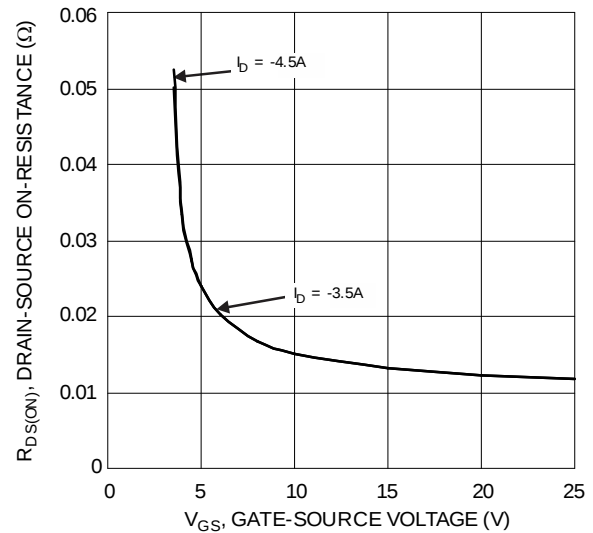


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

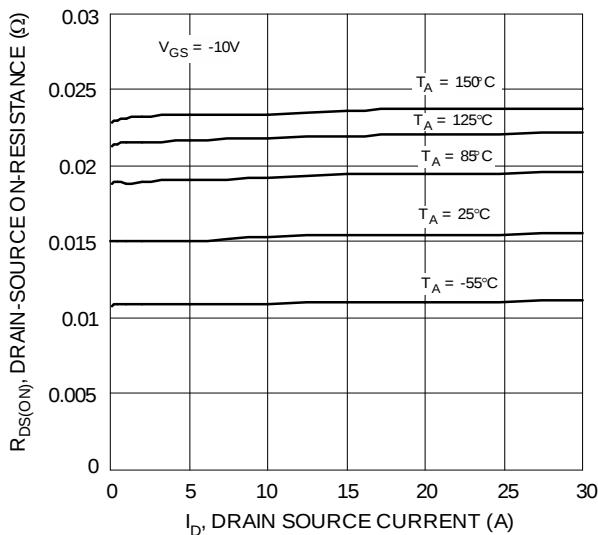


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

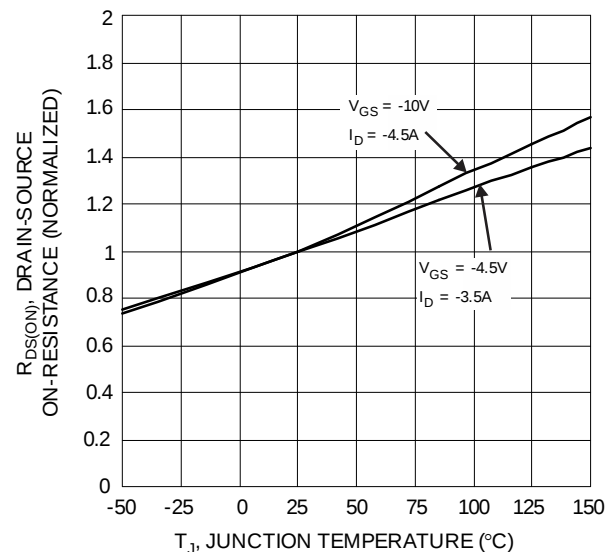
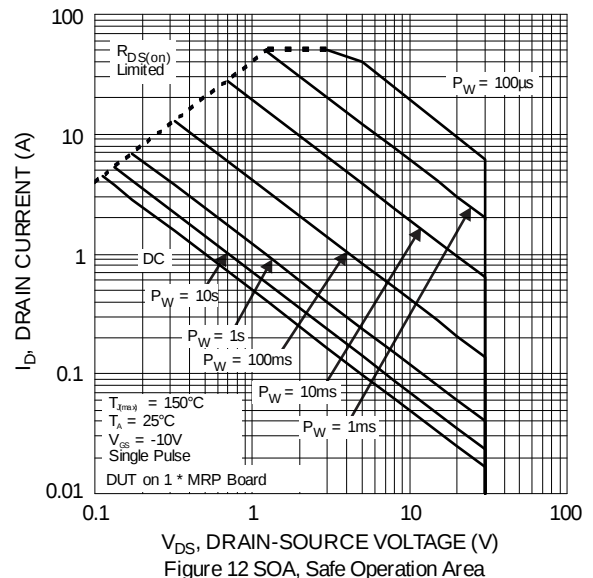
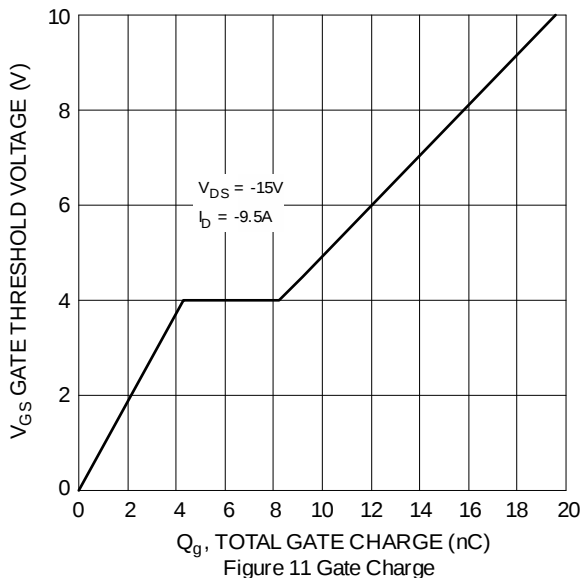
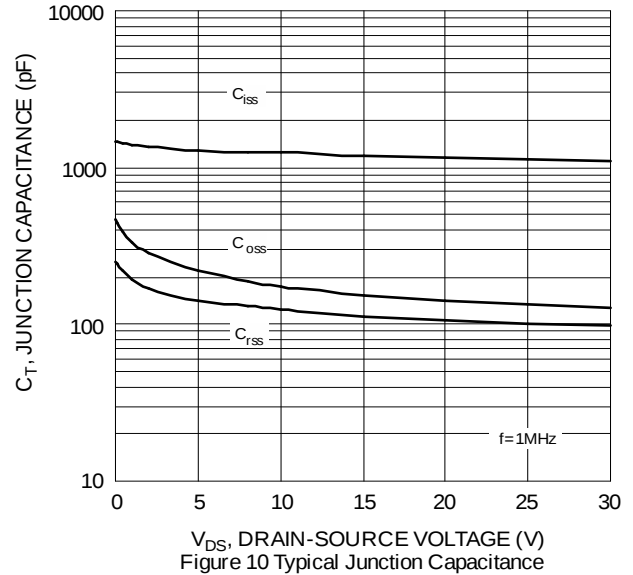
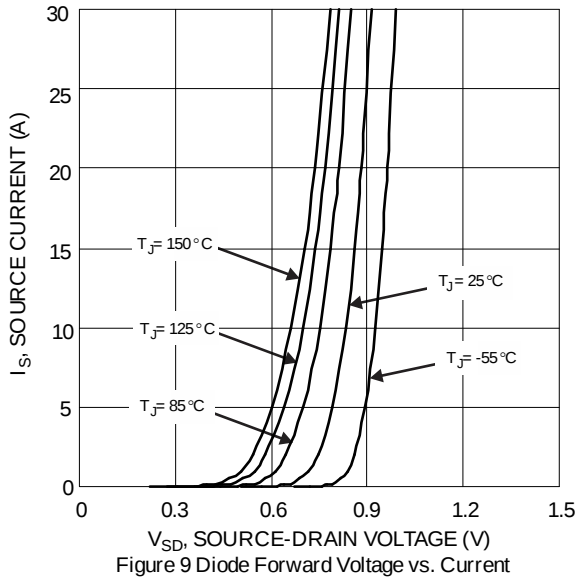
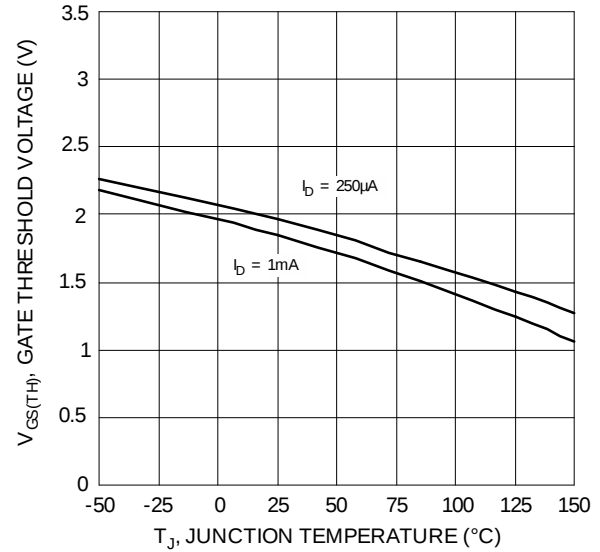
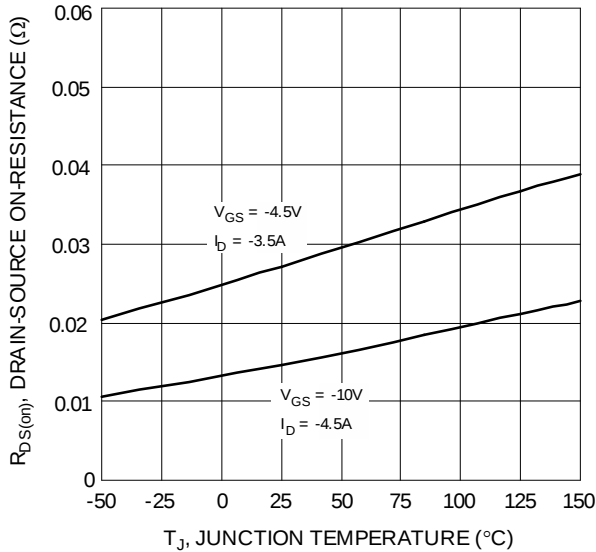
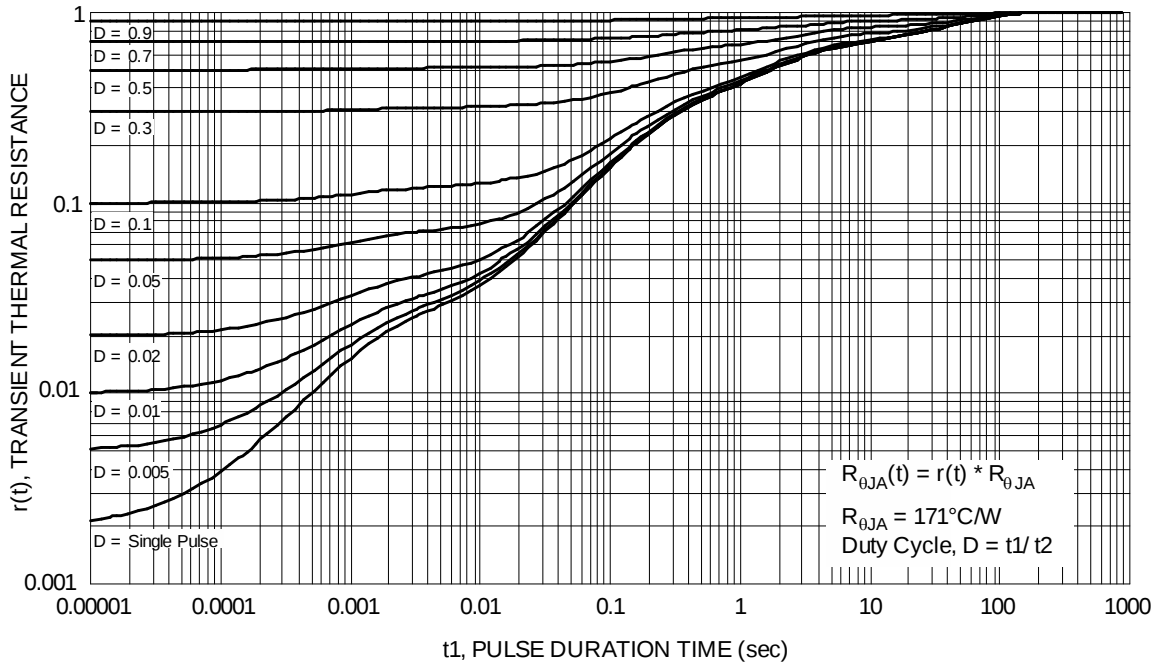


Figure 6 On-Resistance Variation with Temperature

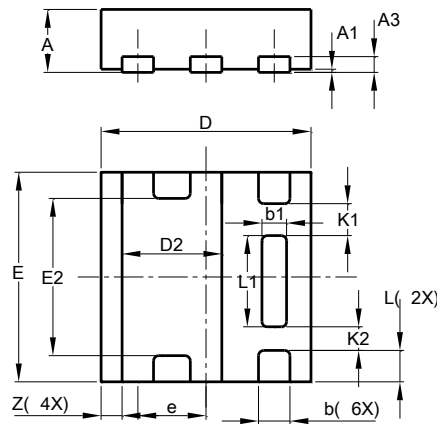




Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type E)

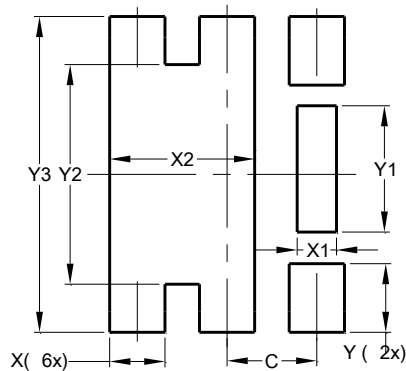


U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	—	—	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	—	—	0.305
K2	—	—	0.225
Z	—	—	0.20
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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